

NCE N-Channel Super Trench Power MOSFET

Description

The series of devices uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

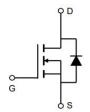
General Features

- V_{DS} =150V, I_D =180A $R_{DS(ON)}$ =4.45m Ω , typical@ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

TO247-3L





Schematic Diagram

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|------------|----------------|-----------|------------|----------|
| NCEP15T18T | NCEP15T18T | TO247-3L | - | - | - |

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|--|------------|--------------|
| Drain-Source Voltage | VDS | 150 | V |
| Gate-Source Voltage | Vgs | ±20 | V |
| Drain Current-Continuous (T _C =25℃) | I _D (T _C =25℃) | 180 | Α |
| Drain Current-Continuous(T _C =100℃) | I _D (T _C =100°C) | 126 | А |
| Pulsed Drain Current | I _{DM} | 720 | А |
| Maximum Power Dissipation (T _C =25℃) | P _D (T _C =25°C) | 360 | W |
| Derating factor | | 2.4 | W/℃ |
| Single pulse avalanche energy (Note 1) | Eas | 1750 | mJ |
| Operating Junction and Storage Temperature Range | T_{J}, T_{STG} | -55 To 175 | $^{\circ}$ C |

Thermal Characteristic

| Thermal Resistance,Junction-to-Case | R _{eJC} | 0.42 | °C/W |
|--|------------------|------|------|
| Thermal Resistance,Junction-to-Ambient(Note 4) | Reja | 40 | °C/W |



Electrical Characteristics (T_C=25°Cunless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|------------------------------------|---------------------|---|----------|------|------|------|
| Off Characteristics | | | • | | | I |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250μA | 150 | | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =150V,V _{GS} =0V | - | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V,V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics | | | <u> </u> | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS}=V_{GS}$, $I_{D}=250\mu A$ | 2.0 | 3.0 | 4.0 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =20A | - | 4.45 | 5.0 | mΩ |
| Forward Transconductance | G FS | V _{DS} =10V,I _D =20A | 70 | - | - | S |
| Dynamic Characteristics | | | | | | |
| Input Capacitance | Clss | \/ 75\/\/ 0\/ | - | 7100 | - | pF |
| Output Capacitance | Coss | V _{DS} =75V,V _{GS} =0V, | - | 890 | - | pF |
| Reverse Transfer Capacitance | C _{rss} | F=1.0MHz | - | 30 | - | pF |
| Switching Characteristics (Note 2) | | | | , | | |
| Turn-on Delay Time | t _{d(on)} | | - | 36 | - | nS |
| Turn-on Rise Time | tr | V_{DD} =75V, I_{D} =20A V_{GS} =10V, R_{G} =4.7 Ω | - | 40 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | | - | 60 | - | nS |
| Turn-Off Fall Time | t _f | | - | 30 | - | nS |
| Total Gate Charge | Qg | \/ -75\/1 -204 | - | 97 | - | nC |
| Gate-Source Charge | Q _{gs} | $V_{DS}=75V,I_{D}=20A,$ | - | 32.5 | - | nC |
| Gate-Drain Charge | Q _{gd} | V _{GS} =10V | - | 22.5 | - | nC |
| Drain-Source Diode Characteristics | | | | | | |
| Diode Forward Voltage | V _{SD} | V _{GS} =0V,I _F =20A | - | | 1.2 | V |
| Diode Forward Current | Is | | - | - | 180 | Α |
| Reverse Recovery Time | t _{rr} | $T_J = 25^{\circ}C, I_F = I_S$ | - | 160 | | nS |
| Reverse Recovery Charge | Qrr | di/dt = 100A/µs | - | 720 | | nC |

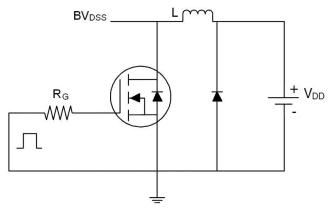
Notes:

- 1. EAS condition : Tj=25 $^{\circ}\!\mathrm{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25 Ω
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=175°C. The SOA curve provides a single pulse rating.
- 4.The value of R_{8JA} is measured in a still air environment with T_{A} =25° C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175° C may be used if the PCB allows it.

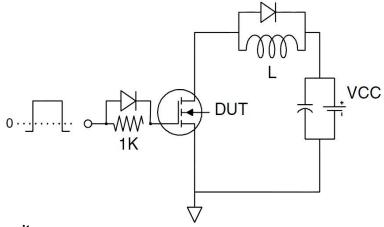


Test Circuit

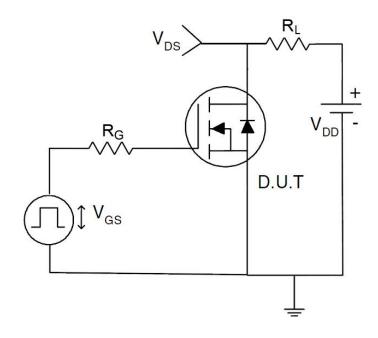
1) E_{AS} test Circuit



2) Gate charge test Circuit

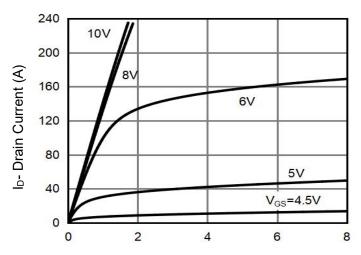


3) Switch Time Test Circuit



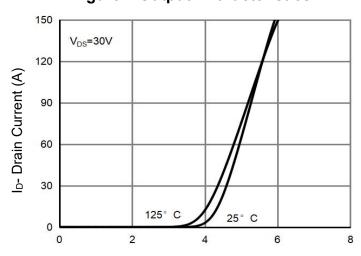


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

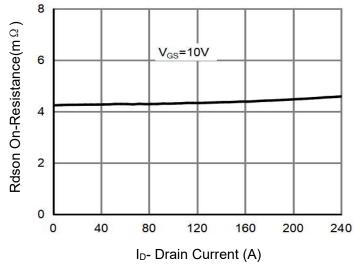


Figure 3 Rdson- Drain Current

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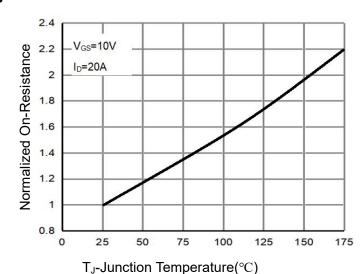


Figure 4 Rdson-JunctionTemperature

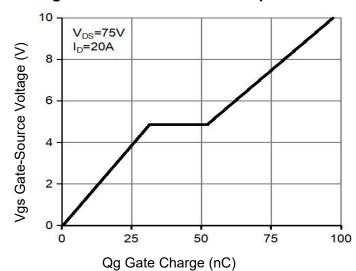


Figure 5 Gate Charge

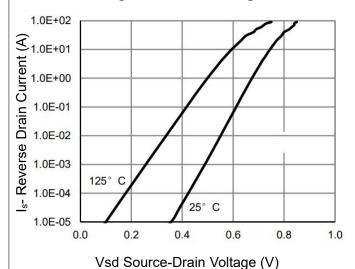
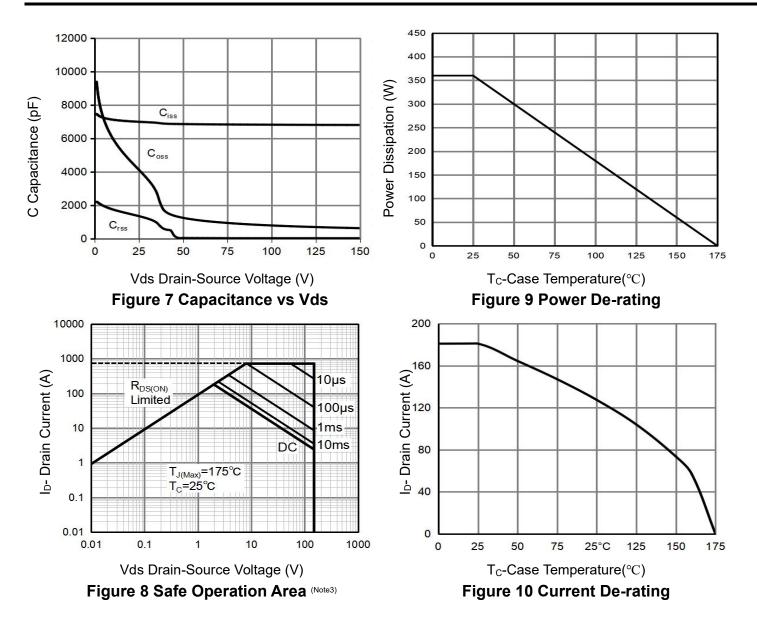


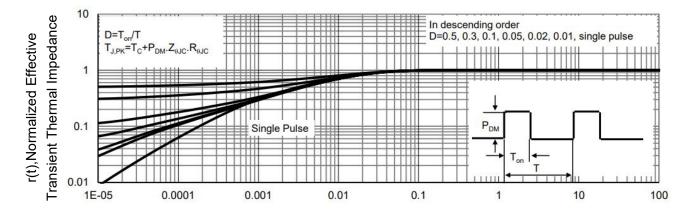
Figure 6 Source- Drain Diode Forward

v1.0

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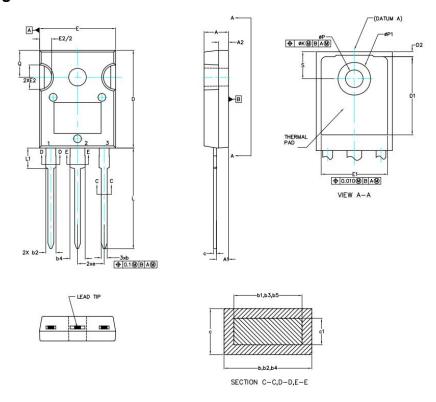


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



TO247-3L Package Information



| S Y | DIMENSIONS | | | | | |
|---------|------------|-----------------|--|----------------|--|--|
| МВС | m | m | inch | | | |
| SYMBOLS | MIN. | MAX. | MIN. | MAX. | | |
| Α | 4.83 | 5.13 | 0.190 | 0.20 | | |
| A1 | 2.21 | 2.59 | 0.087 | 0.102 | | |
| A2 | 1.50 | 2.49 | 0.059 | 0.098 | | |
| b | 0.99 | 1.40 | 0.039 | 0.055 | | |
| b1 | 0.99 | 1.35 | 0.039 | 0.053 | | |
| b2 | 1.65 | 2.39 | 0.065 | 0.094 0.092 | | |
| b3 | 1.65 | 2.34 | 0.065 0.102 0.102 | | | |
| b4 | 2.59 | 3.43 | | 0.135 | | |
| b5 | 2.59 | 3.38 | | 0.133 | | |
| С | 0.38 | 0.89 | 0.015 | 0.035 | | |
| c1 | 0.38 | 0.84 | 0.015 | 0.033 | | |
| D | 19.71 | 20.70 | 0.776 | 0.815 | | |
| D1 | 13.08 | | 0.515 | | | |
| D2 | 0.51 | 1.35 | 0.020 | 0.053 | | |
| Е | 15.29 | 15.87 | 0.602 | 0.625 | | |
| E1 | 13.46 | () | 0.530 | <u> </u> | | |
| E2 | 4.52 | 5.49 | 0.178 | 0.216 | | |
| е | 5.46BSC | | 0.215BSC | | | |
| L | 19.57 | 21.00 | 0.780 | 0.827 | | |
| L1 | 3.71 | 4.29 | 0.146 | 0.169 | | |
| ØΡ | 3.56 | 3.66 | 0.140 | 0.144 | | |
| øP1 | | 7.39 | <u>. </u> | 0.291 | | |
| Q | 5.31 | 5.69 | 0.209 | 0.224 | | |
| S | 5.51BSC | | 0.217BSC | | | |

http://www.ncepower.com

NCEP15T18T

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